PNP Silicon Epitaxial Transistors

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT–223 package which is designed for medium power surface mount applications.

- High Current
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow.

 The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Device Marking:

BCP53T1G = AH

BCP53-10T1G = AH-10

BCP53-16T1G = AH-16

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	-80	Vdc
Collector-Base Voltage	V _{CBO}	-100	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current	I _C	1.5	Adc
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

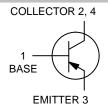
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Surface Mounted)	$R_{ heta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath	T _L	260 10	°C s



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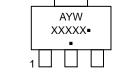
MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



MARKING DIAGRAM



STYLE 1



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code • Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BCP53T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel
NSVBCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Base Breakdown Voltage ($I_C = -100 \mu Adc$, $I_E = 0$)	V _(BR) CBO	-100	_	-	Vdc	
Collector–Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-80	_	-	Vdc	
Collector–Emitter Breakdown Voltage ($I_C = -100 \mu Adc$, $R_{BE} = 1.0 k\Omega$)	V _{(BR)CER}	-100	_	-	Vdc	
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	_	_	Vdc	
Collector–Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	_	-100	nAdc	
Emitter–Base Cutoff Current $(V_{EB} = -5.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	-	-10	μAdc	
ON CHARACTERISTICS						
DC Current Gain $ \begin{array}{l} \text{(I}_{C} = -5.0 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{All Part Types} \\ \text{(I}_{C} = -150 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{BCP53, SBCP53} \\ \text{BCP53-10, SBCP53-10} \\ \text{BCP53-16, SBCP53-16, NSVBCP53-16} \\ \text{(I}_{C} = -500 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{All Part Types} \end{array} $	h _{FE}	25 40 63 100 25	- - - -	- 250 160 250 -	-	
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	V _{CE(sat)}	-	_	-0.5	Vdc	
Base–Emitter On Voltage (I _C = -500 mAdc, V _{CE} = -2.0 Vdc)	V _{BE(on)}	_	_	-1.0	Vdc	
DYNAMIC CHARACTERISTICS	•					
Current–Gain – Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, $f = 35$ MHz)	f⊤	-	50	-	MHz	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

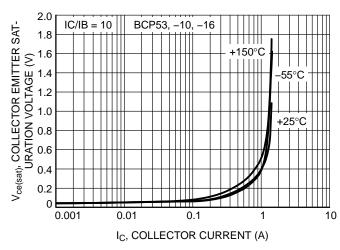


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

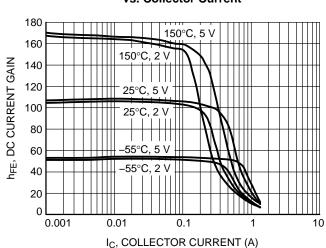


Figure 3. DC Current Gain vs. Collector Current (BCP53-10)

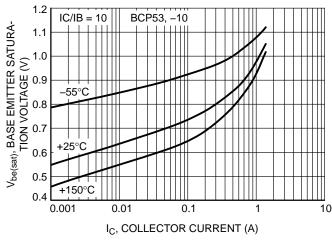


Figure 5. BCP53, –10 Base Emitter Saturation Voltage vs. Collector Current

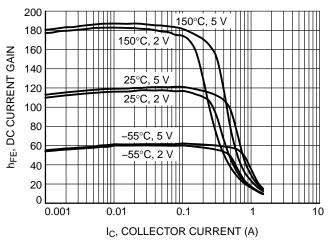


Figure 2. DC Current Gain vs. Collector Current (BCP53)

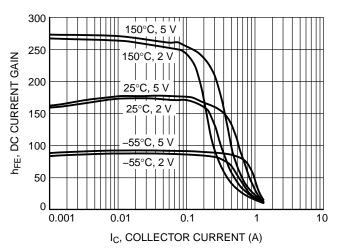


Figure 4. DC Current Gain vs. Collector Current (BCP53-16)

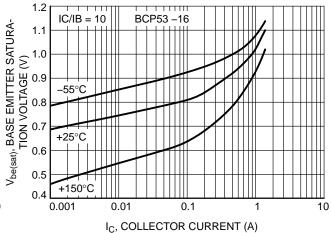
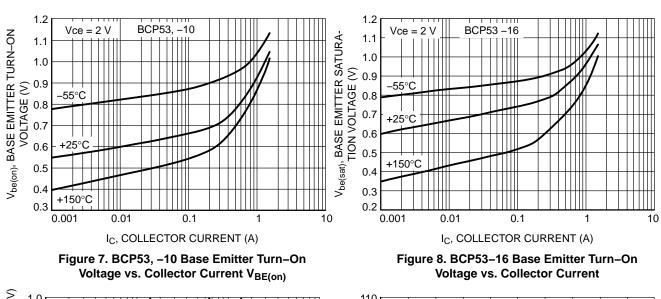


Figure 6. BCP53-16 Base Emitter Saturation Voltage vs. Collector Current

TYPICAL CHARACTERISTICS



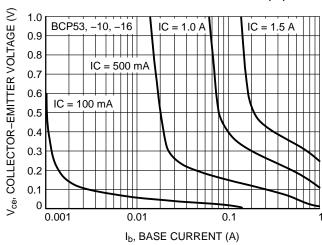


Figure 9. BCP53, -10, -16 Saturation Region

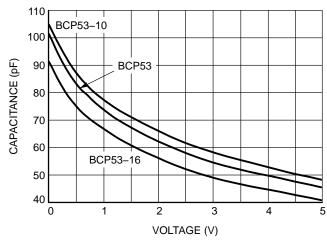


Figure 10. Input Capacitance

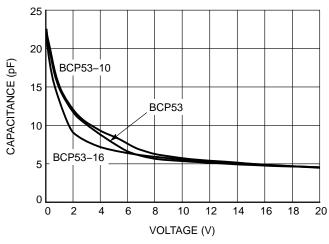


Figure 11. Output Capacitance

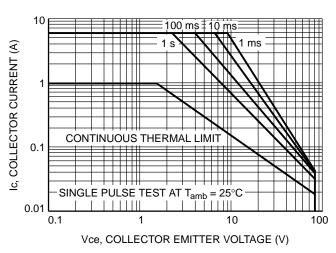
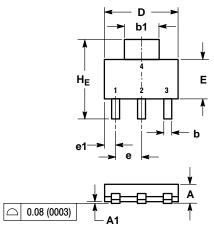


Figure 12. Standard Operating Area

PACKAGE DIMENSIONS

SOT-223 (TO-261)

CASE 318E-04 ISSUE N





NOTES:

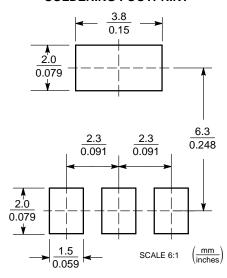
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,
- CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.50	1.63	1.75	0.060	0.064	0.068	
A1	0.02	0.06	0.10	0.001	0.002	0.004	
b	0.60	0.75	0.89	0.024	0.030	0.035	
b1	2.90	3.06	3.20	0.115	0.121	0.126	
O	0.24	0.29	0.35	0.009	0.012	0.014	
D	6.30	6.50	6.70	0.249	0.256	0.263	
E	3.30	3.50	3.70	0.130	0.138	0.145	
е	2.20	2.30	2.40	0.087	0.091	0.094	
e1	0.85	0.94	1.05	0.033	0.037	0.041	
Г	0.20			0.008			
L1	1.50	1.75	2.00	0.060	0.069	0.078	
ΗE	6.70	7.00	7.30	0.264	0.276	0.287	
θ	0°	_	10°	0°	_	10°	

STYLE 1:

- PIN 1. BASE 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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